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学院2021年高水平论文列表 (持续更新中)

2021-07-24 作者: 编辑: 微电子学院 来源: 点击:[178]

2021年:

1. Yang C., Chen W., Fan Y. and Gui P., Design and Characterization of a 10-MHz GaN Gate Driver Using On-Chip Feed-Forward Gaussian Switching Regulation for EMI Reduction. IEEE Journal of Solid-State Circuits. 2021, 56(11): 3521-3532. (JCR Q1, IF=5.013)
2. Zheng X., Liang S. Z., Liu B., et al. Subgraph feature extraction based on multi-view dictionary learning for graph classification. Knowledge-Based Systems. 2021, 214: 106716. (JCR Q1, IF=8.038)
3. Li J. Z., Wang Y. D., Ren Z. G., et al. DOA and Range Estimation Using a Uniform Linear Antenna Array Without A Priori Knowledge of the Source Number. IEEE Trans. Antennas and Propagation. 2021, 69(5):2929-2939. (JCR Q1, IF=4.388)
4. Wu Y. L., Wu J. G., Chen L., et al. Fog Computing Model and Efficient Algorithms for Directional Vehicle Mobility in Vehicular Network. IEEE Trans. Intelligent Transportation Systems. 2021, 22(5): 2599-2614. (JCR Q1, IF=6.492)
5. Zheng X, Liang S, Xiong X. A hardware/software partitioning method based on graph convolution network[J]. Design Automation for Embedded Systems, 2021, Accepted. (JCR Q1, IF=3.815)
6. Shi W. W., Hu L. Z., Liu Y.*, et al. Arithmetic and Logic Circuits Based on ITO-Stabilized ZnO TFT for Transparent Electronics. IEEE Trans. Circuits and Systems I: Regular Papers. 2021, Accepted. (JCR Q2, IF=3.605)
7. Chen Y. Y., Liu Y.*, Wang L., et al. Effect of Hydrogen on Long-term Reliability of InZnO TFTs Characterized by Low-Frequency Noise. IEEE Journal of the Electron Device Society. 2021, 9: 778-782. (JCR Q3, IF=2.484)
8. Liang Z. X., Guo S. Z., Liu D. K., Li J. Z.* Spectral clustering based on high-frequency texture components for face datasets. IET Image Processing. 2021, 15: 2240-2246. (JCR Q3, IF=2.373)

9. He H. Y., Liu Y., Yin J. L., et al. Introducing effective temperature into Arrhenius equation with Meyer-Neldel rule for describing both Arrhenius and non-Arrhenius dependent drain current of amorphous InGaZnO TFTs. Solid-State Electronics. 2021, 181: 108011. (JCR Q3, IF=1.901)
10. Chen Y. Y., Liu Y.*, Ren Y., et al. Temperature dependence of conduction and low frequency noise characteristics in GaN Schottky barrier diodes. Modern Physics Letters B. 2021, 35(8): 2150134. (JCR Q3, IF=1.668)
11. Hu X. H., Chen T. S., Huang H. M., et al. Efficient field-programmable gate array-based reconfigurable accelerator for deep convolution neural network. IET Electronics Letters. 2021, 57(6): 238-240. (JCR Q4, IF=1.314)
12. Huang H. M., Hu X. H., Li X. M., Xiong X. M. An efficient loop tiling framework for convolutional neural network inference accelerators. IET Circuits, Devices & Systems. 2021, Accepted. (JCR Q4, IF=1.297)
13. Huang Y. X., Zhu Z. Q., Cai S. T., Xiong X. M., Liu Y.* Broadband Dual-Polarized Multidipole Antenna for Base Station Applications. International Journal of Antennas and Propagation. 2021, 4206702. (JCR Q4, IF=1.174)

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